L	Hits	Search Text	DB	Time stamp
Number				
1	8	9410821, "9410822"	USPAT;	2003/09/08
			US-PGPUB;	09:43
	1		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	1	(9410821, "9410822") and gas adj2 sensor	USPAT;	2003/09/08
			US-PGPUB;	09:52
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	1	(9410821, "9410822") and gas near3 sensor	USPAT;	2003/09/08
]		US-PGPUB;	09:51
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
6	0	(mosfet with gas adj2 sensor) and hot\$plate	USPAT;	2003/09/08
			US-PGPUB;	10:36
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
7	o	(mosfet with gas adj2 sensor) and hotplate	USPAT;	2003/09/08
			US-PGPUB;	09:51
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
9	16	(hotplate and chemical adj sensor) and gas	USPAT;	2003/09/08
		near3 sensor	US-PGPUB;	10:02
			EPO; JPO;	10101
			DERWENT;	
			IBM_TDB	
10	13	(hotplate and chemical adj sensor) and gas	USPAT;	2003/09/08
		adj2 sensor	US-PGPUB;	10:27
			EPO; JPO;	
i			DERWENT;	
			IBM_TDB	
11	18	(hotplate and chemical adj sensor) and	USPAT;	2003/09/08
		membrane	US-PGPUB;	10:18
;			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
12	o	(mosfet with gas adj2 sensor) and 219/461	USPAT;	2003/09/08
	_		US-PGPUB;	10:07
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
13	o	(hotplate and chemical adj sensor) and	USPAT;	2003/09/08
		219/461	US-PGPUB;	10:07
			EPO; JPO;	10.07
!			DERWENT;	
			· · · · · · · · · · · · · · · · · · ·	
			IBM_TDB	

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15	17	((mosfet with gas adj2 sensor) and	USPAT;	2003/09/08
		membrane) and chemical adj2 sensor	US-PGPUB;	10:36
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
14	18	(mosfet with gas adj2 sensor) and	USPAT;	2003/09/08
		membrane	US-PGPUB;	10:12
	•		EPO; JPO;	10112
			DERWENT;	
			1	
16	15	(/hetalete and chemical adi sense) and are	IBM_TDB	2002/00/09
16	15	((hotplate and chemical adj sensor) and gas	USPAT;	2003/09/08
		near3 sensor) and membrane	US-PGPUB;	11:59
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	1	(9410821, "9410822") and gas with sensor	USPAT;	2003/09/08
			US-PGPUB;	10:25
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
17	13	(hotplate and chemical adj sensor) and gas	USPAT;	2003/09/08
		adj sensor	US-PGPUB;	10:36
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
20	0	(219/461 and hot\$plate) and gas adj sensor	USPAT;	2003/09/08
		(= 10. 101 and notificato) and gao day concer	US-PGPUB;	10:36
			EPO; JPO;	10.55
			DERWENT;	
			1	
21	0	(240/464 and hotenists) and showing a sign	IBM_TDB	0000/00/00
21	"	(219/461 and hot\$plate) and chemical adj2	USPAT;	2003/09/08
		sensor	US-PGPUB;	10:36
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
19	42	219/461 and hot\$plate	USPAT;	2003/09/08
			US-PGPUB;	10:36
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
22	1 1	(219/461 and hot\$plate) and membrane	USPAT;	2003/09/08
			US-PGPUB;	10:37
			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
23	22	(219/461 and hot\$plate) and sensor	USPAT;	2003/09/08
		(US-PGPUB;	10:45
			EPO; JPO;	
1				
1			DERWENT;	
L	L		IBM_TDB	

			_	
24	0	((219/461 and hot\$plate) and sensor) and micro	USPAT; US-PGPUB;	2003/09/08 10:39
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
25	0	((219/461 and hot\$plate) and membrane)	USPAT;	2003/09/08
		and mosfet	US-PGPUB;	10:46
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
5	40	mosfet with gas adj2 sensor	USPAT;	2003/09/08
			US-PGPUB;	10:48
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
26	0	(((hotplate and chemical adj sensor) and gas	USPAT;	2003/09/08
		near3 sensor) and membrane) and	US-PGPUB;	10:58
		membrane with insulator	EPO; JPO;	
			DERWENT;	
27	0		IBM_TDB	0000/00/00
21	"	((mosfet with gas adj2 sensor) and	USPAT;	2003/09/08
		membrane) and membrane with insulator	US-PGPUB;	10:59
			EPO; JPO;	:
			DERWENT; IBM_TDB	
28	o	((hotplate and chemical adj sensor) and	USPAT;	2003/09/08
		membrane) and membrane with insulator	US-PGPUB;	10:59
		monarano, ana monarano with monator	EPO; JPO;	10.55
			DERWENT;	
			IBM_TDB	
29	0	(hotplate and chemical adj sensor) and	USPAT;	2003/09/08
		membrane with insulator	US-PGPUB;	10:59
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
30	0	(9410821, "9410822") and membrane with	USPAT;	2003/09/08
		insulator	US-PGPUB;	10:59
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
31	6	hotplate and membrane with insulator	USPAT;	2003/09/08
		•	US-PGPUB;	11:04
			EPO; JPO;	
			DERWENT;	
20		the Auto-According to the second seco	IBM_TDB	
32	0	(hotplate and membrane with insulator) and	USPAT;	2003/09/08
	1	masking and etching	US-PGPUB;	11:06
			EPO; JPO;	
			DERWENT;	
	<u> </u>		IBM_TDB	

33	2	(hotplate and membrane with insulator) and	USPAT;	2003/09/08
		etching	US-PGPUB;	11:05
			EPO; JPO;	
			DERWENT;	
	,		IBM_TDB	
34	361418	(hotplate and membrane with insulator) and	USPAT;	2003/09/08
		masking or etching	US-PGPUB;	11:06
		_	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
35	O	(hotplate and membrane with insulator) and	USPAT;	2003/09/08
		masking	US-PGPUB;	11:07
			EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
36	0	(monfat with goo adi2 concer) and marking	_	2003/09/08
36		(mosfet with gas adj2 sensor) and masking	USPAT;	
			US-PGPUB;	11:07
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
37	6	219/461 and masking	USPAT;	2003/09/08
			US-PGPUB;	11:09
			EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
38	13	(hotplate and chemical adj sensor) and	USPAT;	2003/09/08
		masking	US-PGPUB;	11:09
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
39	0	hotplate same sensor same masking	USPAT;	2003/09/08
			US-PGPUB;	11:17
			EPO; JPO;	
l .			DERWENT;	
			IBM_TDB	
40	18	hotplate same masking	USPAT;	2003/09/08
		_	US-PGPUB;	11:21
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
41	4	((219/461 and hot\$plate) and sensor) and	USPAT;	2003/09/08
		diode	US-PGPUB;	11:24
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
42	o	((hotplate and chemical adj sensor) and gas	USPAT;	2003/09/08
-	"	adj2 sensor) and diode	US-PGPUB;	11:24
		caja selisorj dilu uloue	1	1 1: 24
			EPO; JPO;	
			DERWENT;	
L	L		IBM_TDB	

43	1	(hotplate and chemical adj sensor) and	USPAT;	2003/09/08
		diode	US-PGPUB;	11:25
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
8	24	hotplate and chemical adj sensor	USPAT;	2003/09/08
		•	US-PGPUB;	11:50
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
18	269	219/461	USPAT;	2003/09/08
			US-PGPUB;	11:52
			EPO; JPO;	11.52
			DERWENT;	
			IBM_TDB	
44	12	(((hotplate and chemical adj sensor) and gas	_	2003/09/08
	12	1	USPAT;	
		near3 sensor) and membrane) and substrate	US-PGPUB;	12:11
			EPO; JPO;	
			DERWENT;	
45	_		IBM_TDB	
45	1	((((hotplate and chemical adj sensor) and	USPAT;	2003/09/08
	*	gas near3 sensor) and membrane) and	US-PGPUB;	12:12
		substrate) and silicon adj carbide	EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
46	1	(hotplate and chemical adj sensor) and	USPAT;	2003/09/08
		silicon adj carbide	US-PGPUB;	12:13
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
47	1	((hotplate and chemical adj sensor) and gas	USPAT;	2003/09/08
		near3 sensor) and silicon adj carbide	US-PGPUB;	12:15
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
48	0	(mosfet with gas adj2 sensor) and silicon	USPAT;	2003/09/08
		adj carbide	US-PGPUB;	12:13
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	•
49	5839	semiconductor with silicon adj carbide	USPAT;	2003/09/08
		-	US-PGPUB;	12:14
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
50	6	(semiconductor with silicon adj carbide) and	USPAT;	2003/09/08
		hotplate	US-PGPUB;	12:15
		•	EPO; JPO;	
			DERWENT;	
			IBM_TDB	

51	12	(semiconductor with silicon adj carbide) and	USPAT;	2003/09/08
		hot\$plate	US-PGPUB;	12:32
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
52	49	4203138, "4234361"	USPAT;	2003/09/08
			US-PGPUB;	12:35
	•		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
54	10	((4203138, "4234361") and hydroxide) and	USPAT;	2003/09/08
		ion	US-PGPUB;	12:38
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
55	2	((4203138, "4234361") and hydroxide) and	USPAT;	2003/09/08
		etching with ion	US-PGPUB;	12:51
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
53	13	(4203138, "4234361") and hydroxide	USPAT;	2003/09/08
			US-PGPUB;	12:38
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
56	23	(mosfet with gas adj2 sensor) and sensor	USPAT;	2003/09/08
		with metal adj oxide	US-PGPUB;	12:52
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
57	21	((mosfet with gas adj2 sensor) and sensor	USPAT;	2003/09/08
		with metal adj oxide) and sensor with	US-PGPUB;	12:52
		polymer	EPO; JPO;	
			DERWENT;	
			IBM_TDB	